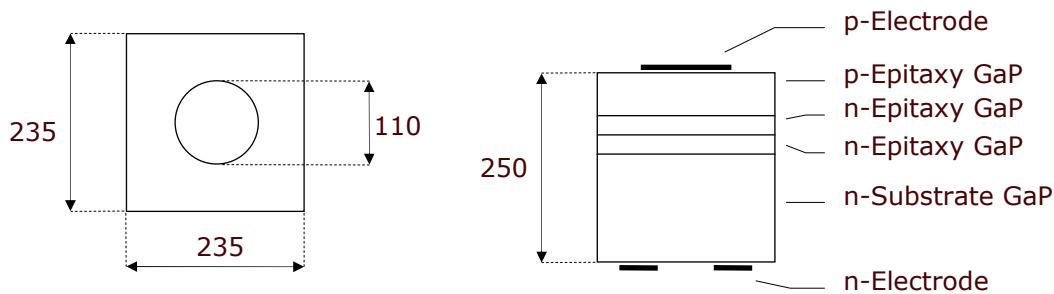


<b>SOFT ORANGE</b>	<b>Item No.: 180622</b>
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1. This specification applies to GaAsP / GaP LED Chips
2. Structure
  - 2.1 Mesa structure
  - 2.2 Electrodes
 

p-side (anode)	Au alloy
n-side (cathode)	Au alloy
3. Outlines (dimensions in microns)



Wire bond contacts can also be square

4. Electrical and optical characteristics (T=25°C)

<i>Parameter</i>	<i>Symbol</i>	<i>Conditions</i>	<i>min</i>	<i>typ</i>	<i>max</i>	<i>Unit</i>
Forward voltage	$V_F$	$I_F = 2 \text{ mA}$		1,85	2,00	V
Reverse current	$I_R$	$V_R = 5 \text{ V}$			10	$\mu\text{A}$
Luminous intensity *	$I_V$	$I_F = 2 \text{ mA}$	180	250		$\mu\text{cd}$
Peak wavelength	$\lambda_p$	$I_F = 2 \text{ mA}$		610		nm

\* On request, wafers will be delivered according to luminous intensity classes  
Brightness measurement at OSA on gold plate

5. Packing
  - 1) wire bond side on top
  - 2) back contact on top

6. Labeling

Type	Lot No.	I <sub>v</sub> typ	min	max	Quantity
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